Special Issue

Wide and Ultrawide Band Gap Semiconductors: Materials and Devices

Message from the Guest Editors

We invite the submission of original research contributions and reviews in areas including, but not limited to, the homoepitaxy and heterojunction of wide-and ultrawide-bandgap semiconductors; metastable phase control and stabilization; quantum-well fabrication and characterization; the development of novel growth and characterization methods; theoretical calculations of the formation and activation of semiconductor defects; novel transport phenomena and defect characterization techniques; device simulation; power device applications, including diodes and metaloxide-semiconductor field-effect transistors (MOSFETs); ultraviolet LEDs and photodetectors; and quantum information devices. Specific research areas may include (but are not limited to) the following:

- Epitaxy of wide- and ultrawide-bandgap semiconductors, including oxides (Ga2O3 and ZnGa2O4), nitrides (GaN, AlGaN, and BN), carbide (SiC), and diamond;
- Heterostructure design, phase control, and interfacedriven phenomena;
- DFT calculations of defects in semiconductors:
- Carrier transport simulation and characterization methods:
- Power devices including diodes and MOSFETs;
- Ultraviolet LEDs and photodetectors.

Guest Editors

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Deadline for manuscript submissions

closed (31 October 2024)



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Message from the Editor-in-Chief

Electronics is a multidisciplinary journal designed to appeal to a diverse audience of research scientists, practitioners, and developers in academia and industry. The journal is devoted to fast publication of latest technological breakthroughs, cutting-edge developments, and timely reviews of current and emerging technologies related to the broad field of electronics. Experimental and theoretical results are published as regular peer-reviewed articles or as articles within Special Issues guest-edited by leading experts in selected topics of interest.

Editor-in-Chief

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